

Title (en)

A HIGH SURFACE AREA SILICON DERIVATIVE FREE MAGNESIUM- TITANIUM CATALYST SYSTEM FOR ETHYLENE POLYMERIZATION AND PROCESS OF PREPARATION THEREOF

Title (de)

SILICIUMDERIVATFREIES MAGNESIUM-TITANKATALYSATORSYSTEM MIT GROSSEM OBERFLÄCHENBEREICH ZUR ETHYLENPOLYMERISATION UND HERSTELLUNGSVERFAHREN DAFÜR

Title (fr)

SYSTÈME DE CATALYSEUR AU TITANE-MAGNÉSIUM DE GRANDE SURFACE EXEMPT DE DÉRIVÉ DE SILICIUM POUR LA POLYMÉRISATION DE L'ÉTHYLÈNE, ET SON PROCÉDÉ DE PRÉPARATION

Publication

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Application

**EP 12815841 A 20120726**

Priority

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Abstract (en)

[origin: WO2013093930A1] The present invention relates to a high surface area silicon derivative free magnesium- titanium catalyst system for ethylene polymerization comprising: magnesium mixed alkoxide and titanium chloride. The present invention also provides a simple process for the preparation of high surface area silicon derivative free magnesium-titanium catalyst system for ethylene polymerization by reacting magnesium alkoxide precursor with titanium compound using dialkyl dialkoxy silane as external donor. The invention further relates to the process for ethylene polymerization using the silicon derivative free magnesium-titanium catalyst system and polyethylene produced" by the catalyst system having narrow molecular weight distribution and higher bulk density.

IPC 8 full level

**C08F 10/00** (2006.01)

CPC (source: EP US)

**C08F 110/02** (2013.01 - EP US)

Citation (search report)

See references of WO 2013093930A1

Citation (examination)

- US 6124412 A 20000926 - BIN-TALEB ABDULMALIK [SA], et al
- EP 0076165 A1 19830406 - TOA NENRYO KOGYO KK [JP]

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